

N-channel 30 V 2 mΩ logic level MOSFET in LFPAK Rev. 4 — 10 March 2011 Produc

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- Class-D amplifiers
- DC-to-DC converters

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	100	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	97	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C		-	1.55	2	mΩ
Dynamic o	characteristics						
Q _{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \underline{\text{Figure } 14};$ $\text{see } \underline{\text{Figure } 15}$		-	7.5	-	nC



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Table 1.	Quick reference data continued						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 14}{100000000000000000000000000000000000$		-	30	-	nC
Avalanch	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} V_{GS} &= 10 \text{ V; } T_{j(init)} = 25 \text{ °C;} \\ I_D &= 100 \text{ A; } V_{sup} \leq 30 \text{ V;} \\ R_{GS} &= 50 \Omega\text{; unclamped} \end{split} $		-	-	151	mJ

[1] Continuous current is limited by package.

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	_	_
2	S	source	mb	
3	S	source		
4	G	gate		d the second sec
mb	D	mounting base; connected to drain		mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

Table 3.	ole 3. Ordering information			
Type numb	er	Package		
		Name	Description	Version
PSMN2R0-3	30YL	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

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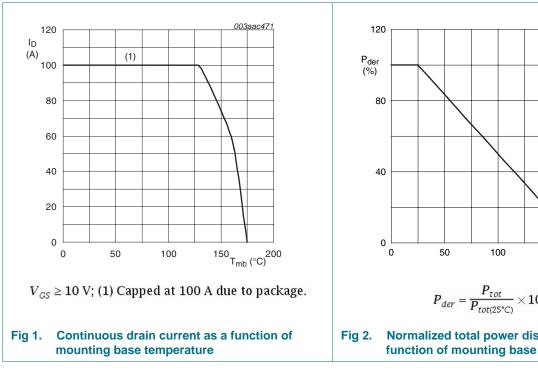
Limiting values 4.

Limiting values Table 4.

In accordance with the Absolute Maximum Rating System (IEC 60134).

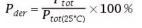
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V _{DSM}	peak drain-source voltage	t _p ≤ 25 ns; f ≤ 500 kHz; E _{DS(AL)} ≤ 280 nJ; pulsed	-	35	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u> -	100	А
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	<u>[1]</u> _	100	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 3</u>	-	667	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	97	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
ls	source current	T _{mb} = 25 °C	<u>[1]</u> _	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	667	А
Avalanche r	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω ; unclamped	-	151	mJ

[1] Continuous current is limited by package.



PSMN2R0-30YL

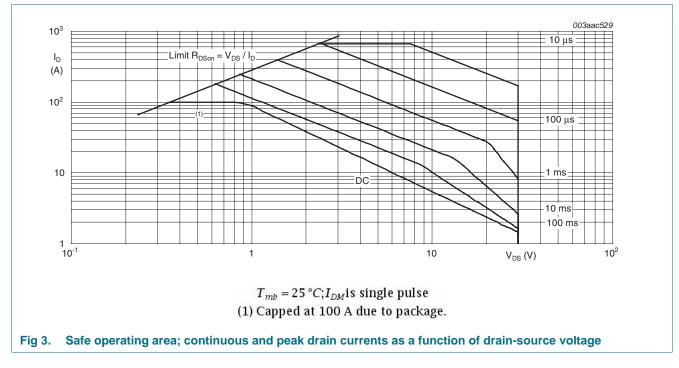
03aa16 150 200 T_{mb} (°C) $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$





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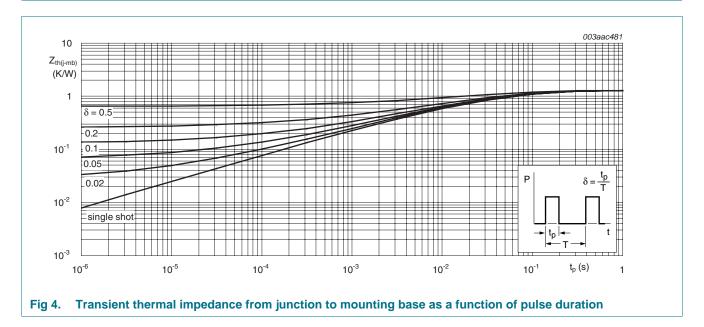
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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.4	1.28	K/W



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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
00()	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C};$ see <u>Figure 12</u>	0.65	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 12</u>	-	-	2.45	V
DSS	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μA
GSS	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon} drain-source on-state	drain-source on-state	V_{GS} = 4.5 V; I_D = 15 A; T_j = 25 °C	-	2.13	2.63	mΩ
resistance		V _{GS} = 10 V; I _D = 15 A; T _j = 150 °C; see <u>Figure 13</u>	-	-	3.3	mΩ
		V_{GS} = 10 V; I _D = 15 A; T _j = 25 °C	-	1.55	2	mΩ
R _G	gate resistance	f = 1 MHz	-	0.75	1.5	Ω
Dynamic ch	aracteristics					
$Q_{G(tot)}$ total gate charge	$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	64	-	nC	
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	59	-	nC
		I_D = 10 A; V_{DS} = 12 V; V_{GS} = 4.5 V; see <u>Figure 14</u>	-	30	-	nC
Q _{GS}	gate-source charge	$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	9.8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	6.6	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	3.2	-	nC
Q _{GD}	gate-drain charge		-	7.5	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 12 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	2.34	-	V
C _{iss}	input capacitance	$V_{DS} = 12 V; V_{GS} = 0 V; f = 1 MHz;$	-	3980	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	857	-	pF
C _{rss}	reverse transfer capacitance		-	347	-	pF
d(on)	turn-on delay time	V_{DS} = 12 V; R _L = 0.5 Ω; V _{GS} = 4.5 V;	-	39	-	ns
r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	65	-	ns
d(off)	turn-off delay time		-	63	-	ns
t _f	fall time		-	28	-	ns

Symbol

Source-drain diode

PSMN2R0-30YL

Тур

Max

Unit

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Min

V_{SD} source-drain voltage I_S = 25 A; V_{GS} = 0 V; T_i = 25 °C; 0.78 1.2 V see Figure 17 $I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$ t_{rr} reverse recovery time 43 -ns $V_{DS} = 20 V$ recovered charge 49 nC Qr --003aac470 003aac474 80 150 10 I_D (A) (A) $V_{GS}(V) = 3$ 60 100 2.8 40 50 2.6 20 T_i = 150 °C 2.4 25 Ċ 2.2 0 0 Λ 1 2 3 0 2 4 6 8 10 V_{DS} (V) $V_{GS}(V)$ $V_{DS} = 10V$ $T_{i} = 25 \,^{\circ}C; t_{p} = 300 \,\mu s$ Transfer characteristics: drain current as a Fig 5. Fia 6. Output characteristics: drain current as a function of gate-source voltage; typical values function of drain-source voltage; typical values 003aac475 003aac477 160 7 R_{DSon} g_{fs} $(m\Omega)$ (S) 140 6 5 120 $V_{GS}(V) = 3 V$ 100 4 3 80 4 2 60 10 40 1 0 50 100 I_D (A) 150 20 40 60 I_D (A) 0 80 $T_j = 25 \,^{\circ}C; t_p = 300 \mu s$ $T_j = 25 \,^{\circ}C; V_{DS} = 15V$ Drain-source on-state resistance as a function Forward transconductance as a function of Fig 7. Fig 8. of drain current; typical values drain current; typical values PSMN2R0-30YL

Characteristics ... continued Table 6.

Tested to JEDEC standards where applicable.

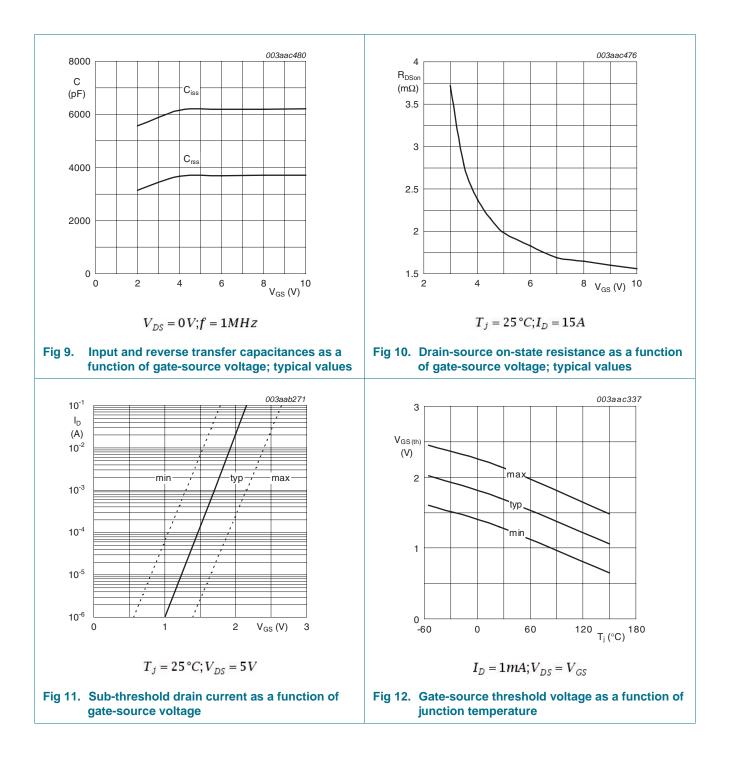
Conditions

Parameter

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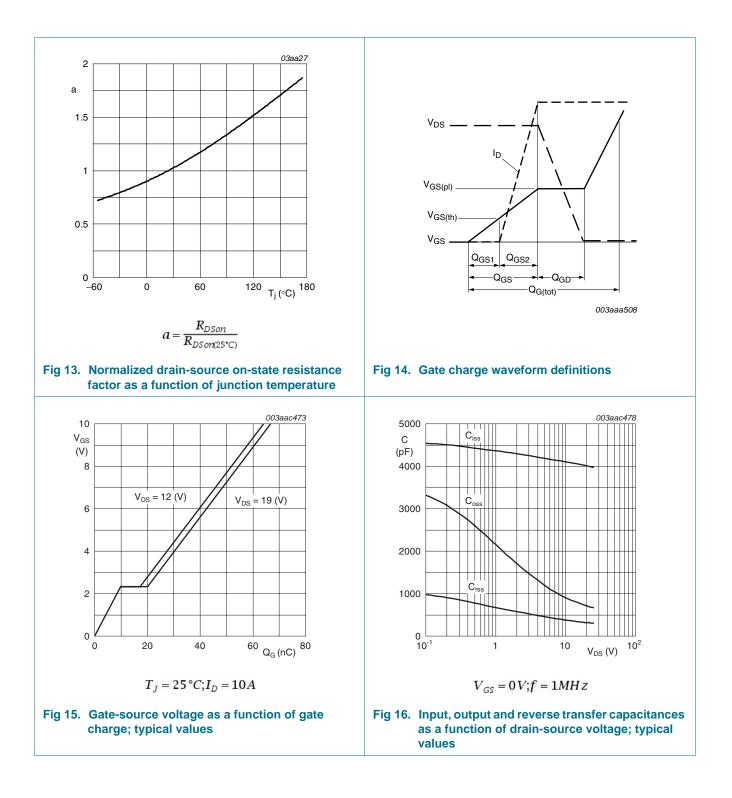
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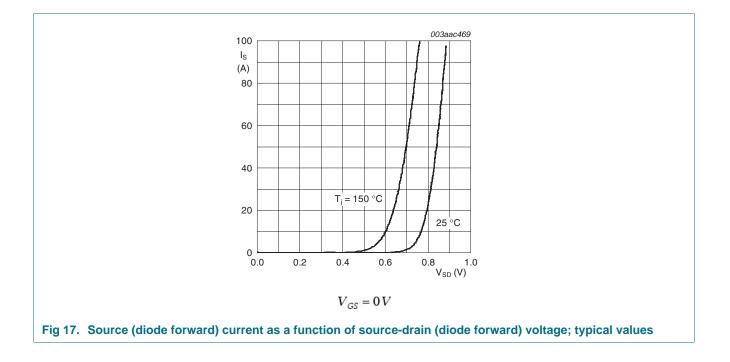
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7. Package outline

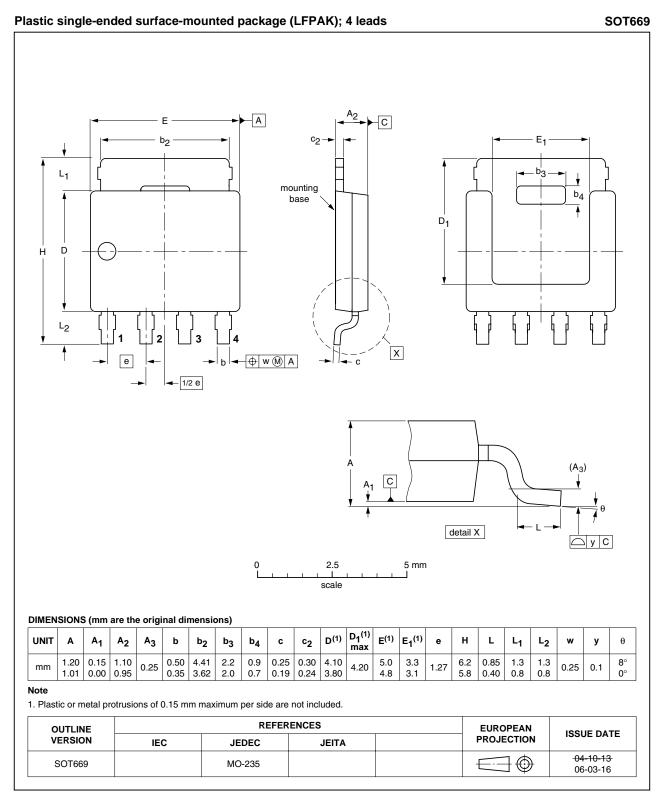


Fig 18. Package outline SOT669 (LFPAK)

PSMN2R0-30YL
Product data sheet

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8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R0-30YL v.4	20110310	Product data sheet	-	PSMN2R0-30YL_3
Modifications:	 Various changes 	to content.		
PSMN2R0-30YL_3	20090105	Product data sheet	-	PSMN2R0-30YL_2

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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